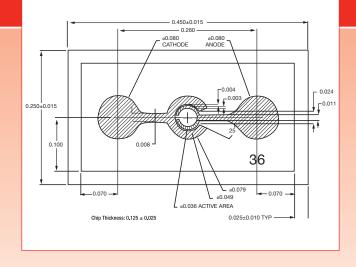
### FCI-InGaAs-36C

## 10Gbps InGaAs Photodiode

OSI Optoelectronics's FCI-InGaAs-36C is an OC-192 (SONET/SDH) capable photosensitive device, exhibiting low dark current and good performance stability.

Both Anode and Cathode contacts appear on the chip's top facet. And it makes ideal component in high-speed optical data transport applications at 10Gbps, responding to a spectral envelop that spans from 910nm to 1650nm.



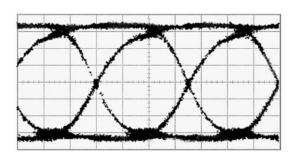
# APPLICATIONS

- High Speed Optical Communications
- OC-192
- Optical Networking
- Optical Measurement

#### FEATURES

- High Speed, 10 Gbps Data Rates
- low Dark Current
- Front Illuminated
- High Responsivity, Typ. 0.8 A/W @1550nm
- Diameter of Light Sensitive area 36µm
- Low Capacitance

# Typical Eye Diagram (10Gbps)<sup>(1)</sup>



Scale: Vertical 100mV/div Horizontal 20.0 ps/div

Electro-Optical Characteristics					T <sub>A</sub> =23°C		
PARAMETERS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Sensing Area Diameter	$AA_{\phi}$			36		μm	
Chip Size				450 x 250		µт x µт	
Responsivity	$R_{\lambda}$	λ=1310nm	0.8	0.85		- A/W	
		λ=1550nm	0.75	0.8			
Capacitance	C <sub>j</sub>	V <sub>R</sub> =5V		0.16	0.2	pF	
Dark Current	I <sub>d</sub>	V <sub>R</sub> =5V		0.5	2	nA	
Breakdown Voltage	V <sub>b</sub>	I <sub>R</sub> =1µA	20			V	
Bandwidth				9		GHz	

(1) Measured with a TIA. Currently FCI-InGaAs-36C is offered in die form only.